

UTC UNISONIC TECHNOLOGIES CO., LTD

UT4392 **Power MOSFET**

30V N-CHANNEL POWER MOSFET

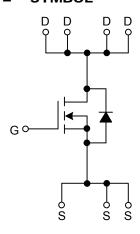
DESCRIPTION

The UT4392 uses UTC advanced technology to provide excellent R_{DS(ON)}, low gate charge and operation with low gate voltages. This device is suitable for being used in such applications: high-Side DC/DC Conversion, notebook and sever.

FEATURES

- * V_{DS}(V)=30V
- * I_D=12.5 A (V_{GS}=10V)
- * High Density Cell Design for Ultra Low On-resistance
- * $R_{DS(ON)}$ <11.5m Ω @ V_{GS} =10V
- * $R_{DS(ON)}$ <16.5m Ω @ V_{GS} =4.5V

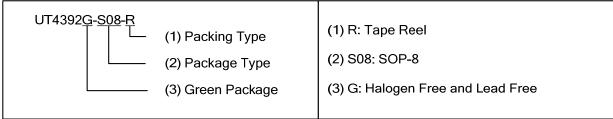


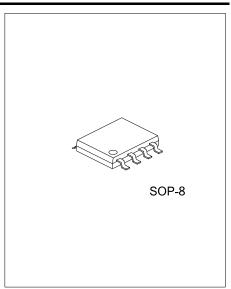


ORDERING INFORMATION

| Ordering Number | Package | Pin Assignment | | | | | | | Da alsia a | |
|-----------------|---------|----------------|---|---|---|---|---|---|------------|-----------|
| | | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | Packing |
| UT4392G-S08-R | SOP-8 | S | S | S | G | D | D | D | D | Tape Reel |

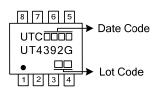
Note: Pin Assignment: G: Gate D: Drain S: Source





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■ MARKING



UT4392 Power MOSFET

■ **ABSOLUTE MAXIMUM RATINGS** (T_A =25°C, unless otherwise specified.)

| PARAMETER | SYMBOL | RATINGS | UNIT |
|---|------------------|--------------------|------|
| Drain-Source Voltage | V_{DSS} | 30 | V |
| Gate-Source Voltage | V_{GSS} | ±20 | V |
| Continuous Drain Current | I _D | 12.5 | Α |
| Pulsed Drain Current | I _{DM} | 50 | Α |
| Power Dissipation(T _A =25°C) | P_D | 3.0 | W |
| Junction Temperature | T_J | +150 | °C |
| Storage Temperature | T _{STG} | -55 ~ + 150 | °C |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

| PARAMETER | SYMBOL | MIN | TYP | MAX | UNIT |
|-----------------------------------|-----------------|-----|-----|-----|------|
| Junction to Ambient (PCB mounted) | θ_{JA} | | | 50 | °C/W |
| Junction to Case | θ _{JC} | | | 25 | °C/W |

Notes: 1. Pulse width limited by the Maximum junction temperature.

■ **ELECTRICAL CHARACTERISTICS** (T_A =25°C, unless otherwise specified.)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT | | | | |
|---|---------------------|---|-----|------|------|------|--|--|--|--|
| OFF CHARACTERISTICS | | | | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0 V, I _D =250 μA | 30 | | | V | | | | |
| Drain-Source Leakage Current | I_{DSS} | V _{DS} =24 V, V _{GS} =0 V | | | 1.0 | μΑ | | | | |
| Gate-Source Leakage Current | I_{GSS} | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | | | ±100 | nΑ | | | | |
| ON CHARACTERISTICS | | | | | | | | | | |
| Gate-Threshold Voltage | $V_{GS(TH)}$ | $V_{DS} = V_{GS}$, $I_{DS} = 250 \mu A$ | 1 | 1.8 | 3 | V | | | | |
| On State Drain Current (Note 1) | $I_{D(ON)}$ | $V_{DS} \ge 5V$, $V_{GS} = 10V$ | 30 | | | Α | | | | |
| Static Drain-Source On-Resistance(Note 1) | R _{DS(ON)} | V_{GS} =10 V, I_{D} =12.5 A | | 9 | 11.5 | mΩ | | | | |
| | | V _{GS} =4.5 V, I _D =10 A | | 13 | 16.5 | mΩ | | | | |
| DYNAMIC PARAMETERS | | | | | | | | | | |
| Input Capacitance | C _{ISS} | V _{DS} =15 V, V _{GS} =0 V, | | 2134 | | pF | | | | |
| Output Capacitance | Coss | -f=1.0MHz, (Note 2) | | 343 | | pF | | | | |
| Reverse Transfer Capacitance | C_{RSS} | | | 134 | | pF | | | | |
| SWITCHING PARAMETERS | | | | | | | | | | |
| Total Gate Charge | Q_G | V _{DS} =15V, V _{GS} =10 V, | | 26 | | nC | | | | |
| Gate Source Charge | Q_GS | $I_D = 15V$, $V_{GS} = 10V$, $I_D = 12.5A$, (Note 2) | | 6 | | nC | | | | |
| Gate Drain Charge | Q_GD | ID = 12.5A, (Note 2) | | 5 | | nC | | | | |
| Turn-ON Delay Time | $t_{D(ON)}$ | | | 17 | | ns | | | | |
| Turn-ON Rise Time | t_R | V _{DD} =15V,I _D =1 A,V _{GEN} =10 V | | 3.5 | | ns | | | | |
| Turn-OFF Delay Time | t _{D(OFF)} | R_G =6 Ω, R_L =15 Ω, (Note 3) | | 40 | | ns | | | | |
| Turn-OFF Fall-Time | t_{F} | | | 6 | | ns | | | | |
| SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS | | | | | | | | | | |
| Diode Forward Voltage | V_{SD} | I _S =2.7 A, V _{GS} =0V | | 0.85 | 1.3 | V | | | | |
| Maximum Body-Diode Continuous Current | Is | (Note 4,5) | | | 2.7 | Α | | | | |

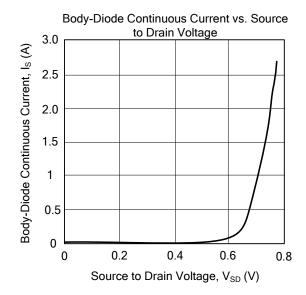
Notes: 1. Pulse Test: PW ≤300µS, Duty Cycle ≤2%

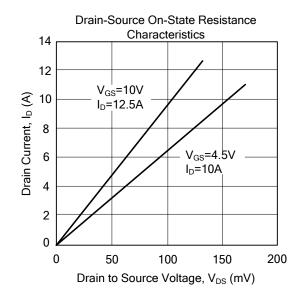
- 2. For DESIGN AID ONLY, not subject to production testing.
- 3. Switching time is essentially independent of operating temperature.
- 4. Pulse width limited by the Maximum junction temperature.
- 5. Surface Mounted on FR4 Board, t ≤ 10 sec.

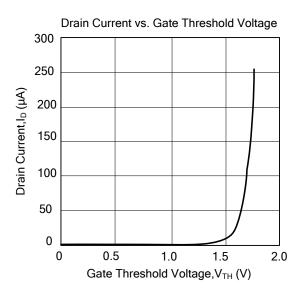
^{2.} Surface Mounted on FR4 Board, t ≤ 10 sec.

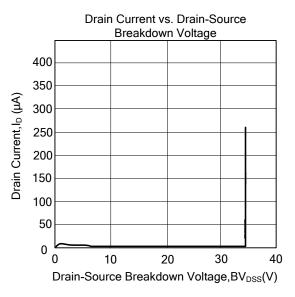
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■ TYPICAL CHARACTERISTICS









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